

ABSTRACT OF THE DISCLOSURE

A post-CMP cleaning process includes brush cleaning a CMPed surface, followed by at least partially drying the CMPed surface, followed by spray cleaning the CMPed surface. A method of cleaning residue from registration alignment markings formed on a semiconductor substrate includes polishing a material within which the registration alignment markings are received with a polishing solution comprising a liquid and a solid, followed by brush cleaning a remaining outermost polished surface, followed by at least partially drying the polished surface, followed by spray cleaning the outermost polished surface. Other aspects and implementations are contemplated.